CONTENTS

SECTION I. INVITED PAPERS 1

I– 1 I. N. STRANSKI, Eine Plauderei über Gleichgewichtsformen von Kristallen 3
I– 2 F. C. FRANK, The future of crystal growth 9
I– 3 K. NASSAU, Dr. A. V. L. Verneuil: the man and the method 12
I– 4 T. SUREK, Molecular phenomena during crystal evaporation 19
I– 5 R. A. LAUDISE, Single crystals for bubble domain memories 27
I– 6 A. AUTHIER, X-ray topography as a tool in crystal growth studies 34
I– 7 D. T. J. HURLE, Hydrodynamics, convection and crystal growth 39
I– 8 F. L. BINSBERGEN, Study of molecular phenomena in the nucleation of crystallisation by computer simulation and application to polymer crystallisation theory 44
I– 9 S. OGAWA and S. INO, Formation of multiply-twinned particles on alkali halide crystals by vacuum evaporation and their structures 48
I–10 K. T. AUST, Principles of crystal growth from the solid state in relation to the preparation of large crystals 57
I–11 J. CORISH and C. D. O'BRIAIN, The growth and dissolution of silver whiskers 62
I–12 M. E. GLICKSMAN, R. J. SCHAEFER and J. A. BLODGETT, Holographic study of crystal growth 68
I–13 M. E. GLICKSMAN and C. L. VOLD, Gradient hot-stage electron microscopy of binary metallic solid/liquid interfaces 73
I–14 R. ROY and W. B. WHITE, Growth of titanium oxide crystals of controlled stoichiometry and order 78
I–15 B. CHALMERS, H. E. LABELLE, JR. and A. I. MLAVSKY, Edge-defined, film-fed crystal growth 84
I–16 R. C. DEVRIES and J. F. FLEISCHER, Phase equilibria pertinent to the growth of cubic boron nitride 88
I–17 E. BUDEVSKI, On the mechanism of electrocrystallization 93
I–18 M. L. TURPIN, Les matériaux composites à fibres 97
I–19 J. STEININGER and T. B. REED, Application of heat pipe technology to crystal growth 106
I–20 M. AVIGNON, Shape stability of a two-dimensional nucleus 113

SECTION II. NUCLEATION, SURFACE DIFFUSION, SIMULATION OF NUCLEATION AND GROWTH 121

II– 1 S. TOSCHEV, A. MILCHEV and S. STOYANOV, On some probabilistic aspects of the nucleation process 123
II– 2 D. KASHCHIEV, Nucleation in external electric field 128
II– 3 I. MARKOV and D. KASHCHIEV, The role of active centers in the kinetics of new phase formation 131
II– 4 R. A. SIGSBEE, Adatom capture and nuclei growth 135
II– 5 H. J. LEAMY and K. A. JACKSON, Surface structure and surface diffusion: the fcc (110) interface 140
II– 6 A. C. ADAMS and K. A. JACKSON, Computer simulation of vapor deposition 144
II– 7 G. H. GILMER and P. BENNEMA, Computer simulation of crystal surface structure and growth kinetics 148
II– 8 F. C. FRANK, An outline of nucleation theory 154

SECTION III. ADSORPTION AND HETEROGENEOUS NUCLEATION FROM THE VAPOUR PHASE 157

III– 1 A. THOMY, J. REGNIER, J. MENAUCOURT et X. DUVAL, Les différentes étapes de la formation d'un film adsorbé de gaz rare ou de méthane sur une surface uniforme de graphite 159
III– 2 J. SUZANNE, G. ALBINET et M. BIENFAIT, Etude par diffraction d'électrons lents de l'adsorption du xénon sur un monocristal du graphite 164
III– 3 R. J. H. VOORHOEVE, R. S. WAGNER and J. N. CARIDES, Study of adsorption and nucleation of cadmium on germanium single crystals by a molecular beam technique 167
III– 4 NGUYEN TAN TUAN ANH, R. CINTI and B. K. CHAKRAVERTY, Condensation of indium films on silicon substrates observed by mass spectrometric technique 174

SECTION IV. CRYSTAL MORPHOLOGY, GROWTH FORMS, EPITAXY 181

IV– 1 D. NENOW, On the variational formulation of the problem of surface equilibrium of crystals 183
IV– 2 G. A. WOLFF, M. WEINSTEIN and B. N. DAS, A unified approach to habit and crystal growth analysis 186
IV– 3 T. OHACHI and I. TANIGUCHI, Controlled filamentary growth of silver from silver compounds 191
IV– 4 J. H. KITTERMAN and D. R. WINDER, Growth of cadmium whiskers in various atmospheres 198
IV– 5 R. HEIMANN, W. FRANKE, and R. LACMANN, Dissolution forms of single crystal spheres of rutile 202
IV– 6 M. LEDÉSERT et M. FREY, Croissance des cristaux de cyanure mercurique orientés par rapport à la matrice de cristaux de leur solvate avec le tétrahydrofuranne 207

IV– 7 E. GILLET and M. GILLET, Croissance continue, à partir de germes à symétrie quinaire, des cristallites "multiples" formés lors de la nucléation hétérogène . . . 212
IV– 8 J. R. ROOS and J. S. VERMAAK, On the growth process of Au and Ag on various air- and vacuum-cleaved alkali halide crystals . . . 217
IV– 9 H. PASCARD, C. QUINTANA, F. HOFFMANN et C. SELLA, Recristallisation de couches minces d'argent sur le mica . . 225

SECTION V. CRYSTAL–MELT INTERFACE, GROWTH OF ICE . . . 229

V– 1 J. ZELL and B. MUTAFTSCHIEV, Simulation of a crystal–melt interface in a monoatomic system . . . 231
V– 2 R. LACMANN and I. N. STRANSKI, The growth of snow crystals . . . 236
V– 3 A. G. CROWTHER, Preliminary investigation into the growth of ice crystals from the vapour in an electric field in the temperature range −11 to −15 °C . . . 241

SECTION VI. CHARACTERIZATION AND ASSESSMENT OF CRYSTAL PERFECTION . . . 245

VI– 1 A. FREUND and J. SCHNEIDER, Two new experimental diffraction methods for a precise measurement of crystal perfection . . . 247
VI– 2 C. G'SELL, B. BAUDELET et G. CHAMPIER, Perfection de cristaux d'aluminium en fonction des traitements thermiques subis . . . 252
VI– 3 H. FEHMER und W. UELHOFF, Die Züchtung versetzungsfreier Kupfereinkristalle . . . 257
VI– 4 C. C. WANG and S. H. MCFARLANE III, Epitaxial growth and characterization of GaP on insulating substrates . . 262
VI– 5 R. F. BELT, R. C. PUTTBACH and D. A. LEPORE, Crystal growth and perfection of large Nd:YAG single crystals . . 268
VI– 6 F. LEFAUCHEUX, Observations de dislocations dans des calcites synthétiques . . . 272
VI– 7 R. LECKEBUSCH und K. RECKER, Perfektion von CaF_2-Einkristallen in Abhängigkeit von der Zuchttechnik . . . 276
VI– 8 D. E. COX and F. C. MERKERT, The preparation, crystal growth and perfection of double halides of $CsNiCl_3$ type 282
VI– 9 I. T. STEINBERGER, E. ALEXANDER, Y. BRADA, Z. H. KALMAN, I. KIFLAWI and S. MARDIX, Growth and perfection of ZnS crystals grown from the vapor phase . . . 285
VI–10 T. OGAWA and M. UCHIDA, Growth and textures of ZnS crystals . . . 292

SECTION VII. VAPOUR GROWTH . . . 295

VII– 1 J. NISHIZAWA, T. TERASAKI and M. SHIMBO, Layer growth in silicon epitaxy . . . 297
VII– 2 J. BLOEM, Doping in chemically vapour deposited epitaxial silicon . . . 302
VII– 3 H. M. MANASEVIT, The use of metal organics in the preparation of semiconductor materials: growth on insulating substrates . . . 306
VII– 4 J. K. KENNEDY and W. D. POTTER, Epitaxial deposition of degenerate n-type layers of Ge on GaAs . . . 315
VII– 5 L. HOLLAN et C. SCHILLER, Etude de l'anisotropie de la croissance épitaxiale de GaAs en phase vapeur . . . 319
VII– 6 J. P. CHANE, L. HOLLAN et C. SCHILLER, Etude de l'épitaxie localisée du GaAs . . . 325
VII– 7 P. MERENDA, Une nouvelle méthode d'épitaxie en phase vapeur d'arséniure de gallium de haute pureté . . . 331
VII– 8 S. IIDA and K. ITO, Morphological studies on selective growth of GaAs . . . 336
VII– 9 CHR. BELOUET, Kinetics of vapour-phase epitaxial growth of $GaAs_{1-x}P_x$ . . . 342
VII–10 T. NISHINAGA, H. OGAWA, H. WATANABE and T. ARIZUMI, Vapor growth of boron monophosphide using open and closed tube processes . . . 346
VII–11 K. PLOOG, P. RAUH, W. STOEGER und H. SCHMIDT, Binäre Verbindungen des Bors mit Elementen der V. Hauptgruppe unter Erhaltung von ikosaedrischen Grundgerüsten: Tetragonales Bornitrid und rhomboedrisches Borphosphid 350
VII–12 M. ILEGEMS, Vapor epitaxy of gallium nitride . . . 360
VII–13 J. P. DISMUKES, W. M. YIM and V. S. BAN, Epitaxial growth and properties of semiconducting ScN . . . 365
VII–14 P. LILLEY, P. L. JONES and C. N. W. LITTING, The epitaxial growth of zinc sulphide on silicon by forced vapour transport in argon flow . . . 371
VII–15 K. NASSAU and J. W. SHIEVER, Vapor growth of II–VI compounds and the identification of donors and acceptors . 375
VII–16 A. KUHN, A. CHEVY and E. LENDVAY, Growth of GaSe single crystals from the vapor phase . . . 380
VII–17 S. I. RADAUTSAN, F. G. DONIKA et I. G. MOUSTIA, Croissance de certains polytypes des phases ternaires semi-conductrices du système zinc–indium–soufre à partir de la phase gazeuse . . . 385
VII–18 G. PAPARODITIS and R. SURYANARAYANAN, Preparation of rare earth chalcogenide thin films by the co-evaporation technique . . . 389
VII–19 H. WIEDEMEIER, E. A. IRENE and A. K. CHAUDHURI, Crystal growth by vapor transport of GeSe, $GeSe_2$, and GeTe and transport mechanism and morphology of GeTe . . . 393
VII–20 M. P. CALLAGHAN and R. W. BRANDER, A new system for the chemical vapour deposition of SiC . . . 397
VII–21 H. K. BOWEN, W. D. KINGERY, M. KINOSHITA and C. A. GOODWIN, Chemical vapor transport of transition metal oxide solid solutions . . . 402
VII–22 J. OUVRARD, R. WANDJI et B. ROQUES, Contribution des réactions chimiques de transport à l'étude structurale des siliciures de fer . . . 406
VII–23 H. S. SHIM and J. G. BYRNE, The effect of substrate temperature and reactant gas pressure on the chemical vapor deposition of tungsten films . . . 410

SECTION VIII. ELECTROCRYSTALLIZATION 415

VIII- 1 I. EPELBOIN, F. LENOIR et R. WIART, Etude par analyse de l'impédance cathodique des processus élémentaires de la croissance cristalline d'un dépôt électrolytique 417

VIII- 2 W. A. SCHULTZE, On the morphology of electrocrystallized copper 421

VIII- 3 U. BERTOCCI, C. BERTOCCI and B. C. LARSON, Observations on the electrocrystallization of copper 427

VIII- 4 H. R. SHANKS, Growth of tungsten bronze crystals by fused salt electrolysis 433

SECTION IX. SOLUTION GROWTH 439

IX- 1 A. GLASNER and M. TASSA, The thermal effects of nucleation and crystallization of KBr solutions 441

IX- 2 F. MUSSARD et S. GOLDSZTAUB, Sur la croissance du chlorate de sodium en solution 445

IX- 3 S. TROOST, Crystal growth of sodium triphosphate hexahydrate from aqueous solutions 449

IX- 4 G. PILKINGTON and W. J. DUNNING, The growth of potassium chloride crystals in the presence of lead 454

IX- 5 S. LE BIHAN et M. FIGLARZ, Croissance de l'hydroxyde de nickel $Ni(OH)_2$ à partir d'un hydroxyde de nickel turbostratique 458

IX- 6 I. F. NICOLAU, M. ITTU et R. DABU, Méthode de croissance en solution des monocristaux par l'addition graduelle d'un réactif 462

IX- 7 E. ACKER, S. HAUSSÜHL und K. RECKER, Züchtung und physikalische Eigenschaften von monoklinem Zinndifluorid 467

IX- 8 H. M. LIAW and J. W. FAUST, JR., Growth kinetics of lead dendrites in gels 471

IX- 9 R. Z. LEGEROS and J. P. LEGEROS, Brushite crystals grown by diffusion in silica gel and in solution 476

SECTION X. INDUSTRIAL BULK CRYSTALLIZATION 481

X- 1 N. J. J. HUIGE and H. A. C. THIJSSEN, Production of large crystals by continuous ripening in a stirred tank . . . 483

X- 2 A. W. NIENOW, P. D. B. BUJAC and J. W. MULLIN, Slip velocities in agitated vessel crystallisers 488

X- 3 E. G. DENK, JR. and G. D. BOTSARIS, Fundamental studies in secondary nucleation from solution 493

X- 4 E. P. K. OTTENS, A. H. JANSE and E. J. DE JONG, Secondary nucleation in a stirred vessel cooling crystallizer . . . 500

X- 5 H. GARABEDIAN and R. F. STRICKLAND-CONSTABLE, Collision breeding of crystal nuclei: sodium chlorate. I 506

X- 6 J. GARSIDE, C. GASKA and J. W. MULLIN, Crystal growth rate studies with potassium sulphate in a fluidized bed crystallizer 510

SECTION XI. HYDROTHERMAL GROWTH 517

XI- 1 Y. TOUDIC, A. REGRENY, M. PASSARET, R. AUMONT et J. F. BAYON, Nouveau type d'appareillage appliqué à la croissance hydrothermale de monocristaux de cinabre de grandes dimensions 519

XI- 2 M. PASSARET, Y. TOUDIC, A. REGRENY, R. AUMONT et J. F. BAYON, Recristallisation de TiO_2, GeO_2, SiO_2, $Si_{1-x}Ge_xO_2$ en solutions hydrothermales fluorées 524

XI- 3 M. L. BARSUKOVA, V. A. KUZNETSOV, A. N. LOBACHEV and YU. V. SHALDIN, Hydrothermal crystallisation and some properties of bismuth titanates 530

XI- 4 R. DHARMARAJAN, R. F. BELT and R. C. PUTTBACH, Hydrothermal and flux growth of zircon crystals 535

XI- 5 A. N. LOBACHEV, L. N. DEMIANETS, I. P. KUZMINA and E. N. EMELIANOVA, Investigation of the solubility and crystallization kinetics of sodium–zinc germanate (Na_2ZnGeO_4) under hydrothermal conditions 540

XI- 6 NGUYEN DUC CHINH, Méthode de dopage au chrome dans la préparation du rubis hydrothermal 545

XI- 7 S. MROCZKOWSKI and J. ECKERT, Hydrothermal growth of single crystals of heavy rare earth hydroxides . . . 549

SECTION XII. FLUX GROWTH 553

XII- 1 D. ELWELL and R. D. DAWSON, The variation of crystal growth rate with supersaturation in fluxed melts . . . 555

XII- 2 H. J. SCHEEL, Accelerated crucible rotation: a novel stirring technique in high-temperature solution growth . . . 560

XII- 3 W. TOLKSDORF and F. WELZ, The effect of local cooling and accelerated crucible rotation on the quality of garnet crystals 566

XII- 4 A. BROCHIER, P. COEURE, B. FERRAND, J. C. GAY, J. C. JOUBERT, J. MARESCHAL, J. C. VIGUIE, J. C. MARTIN-BINACHON et J. SPITZ, Hétéroépitaxie de couches minces de grenat de fer–yttrium par méthode de flux et synthèse hydrothermale 571

XII- 5 J. M. ROBERTSON and B. W. NEATE, Some observations on the growth of YIG under oxygen pressure by the "fluxed melt" technique 576

XII- 6 M. SCHIEBER, A. GRILL and Y. AVIGAL, Flux growth and magnetic characterization of calcium–silicon substituted ytterbium and yttrium iron garnets 579

XII- 7 R. KRISHNAN, Some features of the growth of single crystals of the $Y_3Fe_{5-x}Cr_xO_{12}$ system 582

XII- 8 H. MAKRAM, L. TOURON and J. LORIERS, Phase relations in the system Fe_2O_3–B_2O_3 and its application in single crystal growth of $FeBO_3$ 585

XII- 9 G. GARTON, S. H. SMITH and B. M. WANKLYN, Crystal growth from the flux systems PbO–V_2O_5 and Bi_2O_3–V_2O_5 588

XII-10 J. LORIERS et M. VICHR, Synthèse de monocristaux de vanadate d'yttrium par la méthode de tirage en flux . . . 593

XII-11 C. BÉLIN, J. J. BRISSOT and R. E. JESSE, The growth of calcite single crystals by travelling solvent zone melting . . 597

XII–12 L. Vu Tien, A. Grandin de l'Eprevier, V. Gabis et A. M. Anthony, Amélioration de la méthode des flux, synthèse et purification d'un minéral naturel: la forstérite 601
XII–13 J. W. Goodrum, Solution top-seeding: growth of GeO_2 polymorphs 604

SECTION XIII. MELT GROWTH – BASIC STUDIES AND SEMICONDUCTORS 609

XIII– 1 J. R. Carruthers and M. Grasso, The stabilities of floating liquid zones in simulated zero gravity 611
XIII– 2 T. Arizumi and N. Kobayashi, Theoretical studies of the temperature distribution in a crystal being grown by the Czochralski method 615
XIII– 3 K. J. Gärtner, K. F. Rittinghaus, A. Seeger and W. Uelhoff, An electronic device including a TV-system for controlling the crystal diameter during Czochralski growth 619
XIII– 4 D. F. O'Kane, T. W. Kwap, L. Gulitz and A. L. Bednowitz, Infrared TV system of computer controlled Czochralski crystal growth 624
XIII– 5 J. B. Mullin, W. R. Macewan, C. H. Holliday and A. E. V. Webb, Pressure balancing: a technique for suppressing dissociation during the melt-growth of compounds 629
XIII– 6 B. C. Grabmaier and J. G. Grabmaier, Dislocation-free GaAs by the liquid encapsulation technique 635
XIII– 7 J. B. Mullin, A. Royle, B. W. Straughan, P. J. Tufton and E. W. Williams, Crystal growth and properties of group IV doped indium phosphide 640
XIII– 8 A. R. von Neida, L. J. Oster and J. W. Nielsen, Liquid encapsulated growth of GaP from non-stoichiometric melts 647
XIII– 9 A. R. Peaker, P. D. Sudlow and A. Mottram, Solution growth of gallium phosphide p–n junctions by liquid phase epitaxy 651
XIII–10 J. Steininger and A. J. Strauss, Phase diagrams and crystal growth of pseudobinary alloy semiconductors . . . 657
XIII–11 E. André, J. M. LeDuc and M. Mahieu, Liquid phase epitaxy of $Ga_{1-x}Al_xAs$ 663
XIII–12 R. Ueda, O. Ohtsuki, K. Shinohara and Y. Ueda, Crystal growth of $Hg_{1-x}Cd_xTe$ using Te as a solvent . . . 668

SECTION XIV. MELT GROWTH – MAINLY OXIDES 673

XIV– 1 J. Aubrée, Tirage du niobate de calcium monocristallin dopé au néodyme 675
XIV– 2 M. Takahashi, S. Nanamatsu and M. Kimura, The growth of ferroelectric single crystal $Sr_2Nb_2O_7$ by means of the floating zone technique 681
XIV– 3 R. S. Feigelson, G. W. Martin and B. C. Johnson, Crystal growth and properties of some alkali metal metavanadates 686
XIV– 4 J. Billingham, P. S. Bell and M. H. Lewis, The crystal growth of transition metal interstitial compounds by a floating zone technique 693
XIV– 5 D. Mateika, Growth of MnTe single crystals from nonstoichiometric melts by liquid encapsulation 698
XIV– 6 J. W. Nielsen and S. L. Blank, Crystal growth and phase equilibrium studies in the system $(R.E.)_2O_3$–Fe_2O_3 . . 702
XIV– 7 J. Daval, D. Challeton et J. Mareschal, Croissance de monocristaux d'orthoferrite d'yttrium par tirage Czochralski 706
XIV– 8 F. B. Khambatta, P. J. Gielisse, M. P. Wilson, Jr., J. A. Adamski and Ch. Sahagian, Initial thermal model of the flame fusion crystal growth process 710
XIV– 9 J. Ricard et A. Cioccolani, Croissance industrielle et caractérisation de grands monocristaux de saphir par la méthode de Verneuil 718
XIV–10 R. Falckenberg, Growth of stoichiometric Mg–Al spinel single crystals by a modified Verneuil technique . . . 723
XIV–11 A. Freund, P. Guinet, J. Mareschal, F. Rustichelli et F. Vanoni, Cristaux à gradient de maille 726

SECTION XV. EUTECTICS, DENDRITES, INCLUSIONS 731

XV– 1 G. Lesoult, Thermodynamique de la solidification eutectique 733
XV– 2 R. S. Fidler, M. N. Croker and R. W. Smith, The thermodynamics and morphologies of eutectics containing compound phases 739
XV– 3 M. Durand-Charre and F. Durand, Effects of growth rate on the morphology of monovariant eutectics: MnSb–(Sb, Bi) and MnSb–(Sb, Sn) 747
XV– 4 P. Combrade et M. Turpin, Solidification monovariante d'alliages ternaires; application à la fusion de zone . . . 751
XV– 5 J.-C. Hubert, W. Kurz et B. Lux, Croissance en solidification dirigée de l'eutectique quasi-binaire Ni_3Al–Ni_3Ta 757
XV– 6 A. T. Chapman, R. J. Gerdes, J. C. Wilson and G. W. Clark, Unidirectional solidification behavior in refractory oxide–metal systems 765
XV– 7 H. M. Liaw and J. W. Faust, Jr., Effect of modes of crystallization on habit and morphology of copper dendrites 772
XV– 8 J. Cissé, G. F. Bolling and H. W. Kerr, Crystallographic orientations between aluminum grown from the melt and various titanium compounds 777
XV– 9 A. A. Tzavaras and J. F. Wallace, Cast steel structures grown under fluid flow 782
XV–10 W. R. Wilcox, Movement of liquid inclusions by centrifugation 787
XV–11 H. E. Cline and T. R. Anthony, The migration of liquid droplets in solids 790

SECTION XVI. SEGREGATION AND DEFECTS 795

XVI– 1 A. S. Yue and J. T. Yue, The effect of concentration and temperature gradients on solute redistribution . . . 797
XVI– 2 C. Potard, Calcul des conditions de croissance de cristaux en solution 804

XVI– 3 B. D. Warr and R. W. Smith, The orientation-dependence of the partition coefficient in zinc-base alloy single crystals 810
XVI– 4 J. Deloche, Y. Malmejac et B. Schaub, Etude des conditions de croissance de monocristaux de beryllium . . . 814
XVI– 5 H. C. Casey, Jr. and M. B. Panish, The influence of the electrical properties of the solid phase on impurity incorporation during crystal growth 818
XVI– 6 P. Bottelier et F. Bouillon, Structure de monocristaux d'alliages cuivre–nickel fabriqués par la technique de Bridgman 823

SECTION XVII. SOLID STATE TRANSFORMATIONS 827
XVII– 1 Y. Monfort, A. Maisseu, G. Allais et A. Deschanvres, Croissance orientée des sous oxydes de niobium dans la matrice de niobium 829
XVII– 2 F. Blanié et J. Le Héricy, Croissance, par recristallisation secondaire, de gros cristaux exempts de macles dans le cuivre purifié par fusion de zone 834
XVII– 3 E. Grochowski and W. Brenner, The effects of selenide molecular transformations on electrical resistivity . . . 843

Report on the Activities of the ICCG–3 General Assembly and the IOCG 849

List of authors quoted in references 851

Author index 864

Subject index 872

Compound index 875